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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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09/037,674

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HIDEKI MIZUHARA

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7590

02/04/2003

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EXAMINER

NADAV, ORI

ART UNIT

PAPER NUMBER

2811

DATE MAILED: 02/04/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/037,674

Applicant(s)

MIZUHARA ET AL.

Examiner

ori nadav

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 10 December 2002.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 16-33 is/are pending in the application.
- 4a) Of the above claim(s) 16-24 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 25-33 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- ☐ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- ☐ Interview Summary (PTO-413) Paper No(s) _____
- ☐ Notice of Informal Patent Application (PTO-152)
- ☐ Other:

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DETAILED ACTION

Claim Objections

1. Claims 25-33 are objected to because of the following informalities: Claims 25 and 31 recite the limitation "the surface" in lines 5, respectively. There is insufficient antecedent basis for this limitation in the claim.

Appropriate correction is required.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

3. Claims 25-33 are rejected under 35 U.S.C. 102(b) as being anticipated by Okumura et al. (4,984,055).

Okumura et al. teach in figure 13D and related text a semiconductor device comprising a semiconductor substrate 1, an interlayer insulating film (ILD) 12 on the substrate, wirings 16 located on the ILD 12 and a passivation layer covering a surface of the ILD

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and the wirings, including a first insulating film 13 that is a modified SOG containing boron impurities (column 16, line 15), and a second insulating film 14 comprising oxide having a hygroscopicity lower than the first insulating film and being located on at least one of an upper side and lower side of the first insulating film.

Although Okumura et al. do not explicitly state that layers 13 and 15, respectively, are passivation layers, layers 13 and 15 meet the functional limitations of the claims since layers 13 and 15 protect the device.

Regarding the claimed limitations of “a modified SOG film of an organic SOG film”, these would not carry patentable weight in this claim drawn to a structure, because distinct structure is not necessarily produced by forming a modified SOG film from an organic SOG film. Note that a “product by process” claim is directed to the product per se, no matter how actually made, *In re Hirao*, 190 USPQ 15 at 17 (footnote 3). See also *In re Brown*, 173 USPQ 685; *In re Luck*, 177 USPQ 523; *In re Fessmann*, 180 USPQ 324; *In re Avery*, 186 USPQ 161; *In re Wertheim*, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and *In re Marosi et al.*, 218 USPQ 289, all of which make it clear that it is the patentability of the final product per se which must be determined in a “product by process” claim, and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether claimed in “product by process” claims or not. Note that the applicant has the burden of proof in such cases, as the above case law makes clear.

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Regarding claims 26, 29 and 32, although Okumura et al. do not explicitly state that silicon oxide has a hygroscopicity lower than boron doped SOG, this feature is inherent in Okumura et al.'s device, because it is well known in the art that silicon oxide has a hygroscopicity lower than boron doped SOG, of which judicial notice is taken.

Claim Rejections - 35 USC § 103

4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which the subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

5. Claims 25-33 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakano (JP 6-291202) in view of Okumura et al.

Nakano teaches in figure 1b and related text a semiconductor device comprising a semiconductor substrate 11, an insulating film 12 on the substrate, wirings 13 located on the insulating film 12 and a passivation layer covering a surface of the insulating film and the wirings, including a first insulating film 15 that is a modified SOG containing boron impurities (abstract) and a second insulating film 16 comprising oxide having a hygroscopicity lower than the first insulating film and being located on at least one of an upper side and lower side of the first insulating film..

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Although Nakano does not explicitly state that layers 15 and 16, respectively, are passivation layers, layers 15 and 16 meet the functional limitations of the claims since layers 15 and 16 protect the device.

Nakano does not state that insulating film 12 is an interlayer insulating film. Okumura et al. teach in figure 13D an interlayer insulating film (ILD) 12 located between the semiconductor substrate 1 and wirings 16. It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use an interlayer insulating film as the insulating film in Nakano's device in order to provide good isolation between the wiring layers and the active regions in the semiconductor substrate.

Regarding the claimed limitations of "a modified SOG film of an organic SOG film", these would not carry patentable weight in this claim drawn to a structure, because distinct structure is not necessarily produced by forming a modified SOG film from an organic SOG film. Note that a "product by process" claim is directed to the product per se, no matter how actually made, *In re Hirao*, 190 USPQ 15 at 17 (footnote 3). See also *In re Brown*, 173 USPQ 685; *In re Luck*, 177 USPQ 523; *In re Fessmann*, 180 USPQ 324; *In re Avery*, 186 USPQ 161; *In re Wertheim*, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); and *In re Marosi et al.*, 218 USPQ 289, all of which make it clear that it is the patentability of the final product per se which must be determined in a "product by process" claim, and not the patentability of the process, and that an old or obvious product produced by a new method is not patentable as a product, whether

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claimed in "product by process" claims or not. Note that the applicant has the burden of proof in such cases, as the above case law makes clear.

Regarding claims 26, 29 and 32, although Nakano does not explicitly state that silicon oxide has a hygroscopicity lower than boron doped SOG, this feature is inherent in Nakano's device, because it is well known in the art that silicon oxide has a hygroscopicity lower than boron doped SOG, of which judicial notice is taken.

Response to Arguments

6. Applicant argues on pages 3- 4 that Okumura et al. do not teach a passivation film located on the silicide (wiring) layer.

In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., a passivation film located on the silicide (wiring) layer) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993). Claims 25 and 31 recite a passivation layer covering the surface of the ILD and the wirings. Okumura et al. teach a passivation layer 13, 14 and covering the surface (the top surface) of the ILD 12 and the surface (bottom and side surfaces) of the wirings 16.

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Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to *Examiner Nadav* whose telephone number is **(703) 308-8138**. The Examiner is in the Office generally between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas, can be reached at **(703) 308-2772**.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Technology Center Receptionists** whose telephone number is **308-0956**

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A handwritten signature in black ink, appearing to read "Ori Nadav". The signature is fluid and cursive, with the first name "Ori" and the last name "Nadav" clearly distinguishable.

O.N.
January 31, 2003

ORI NADAV
PATENT EXAMINER
TECHNOLOGY CENTER 2800